

Attorney's Docket No.: 07977/226002/US364801

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Hisashi Ohtani Art Unit: 1765
Serial No.: 09/596,755 Examiner: Robert Kunemund
Filed : June 15, 2000 Confirmation No.: 3261
Title : MANUFACTURING METHOD OF SEMICONDUCTOR AND
MANUFACTURING METHOD OF SEMICONDUCTOR DEVICE^{2,4}

Commissioner for Patents
Washington, D.C. 20231

RESPONSE

In response to the official action mailed 05/06/02, paper
no. 14 in the above referenced case, please amend the
application as follows:

In the claims:

Please amend claims 2, 4, 8, 10, 14, 16, 20, 22, 25, 29,
30, 32, 36, 37, 41, and 42 as follows:

2. (Amended) A method for manufacturing a semiconductor
device comprising steps of:

forming a semiconductor film comprising silicon over a
substrate; and

irradiating said semiconductor film by scanning with at least
first and second pairs of linear infrared lights in a
predetermined direction, intensities of the second pair of

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